

Effect of ZnO doping co-carried out by Co-Cu on nonlinear optical properties prepared by the spin coating method

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Abstract

In the present work, thin films of ZnO co-doped with Co and Cu cations were obtained on glass substrate, combining the sol gel process and spin-coating technique. For the compound, the general chemical formula used was: $Zn_{1-x-z}Co_xCu_zO$, [(x; z)=(0.00; 0.00), (0.02; 0.02), (0.04; 0.04) and (0.06; 0.06)]. For pure ZnO film, the surface morphology is composed by small spherical grains that present interstitial spaces, while the films obtained from the simultaneous Co and Cu insertion in the ZnO structure are more dense and interstitial spaces disappear. For all films, the X-ray diffraction patterns testify the monophasic phase formation, typical of the hexagonal structure of ZnO. In addition, the films presented preferential orientation in the (002) direction. It was demonstrated that the Zn^{2+} cations by Co²⁺ and Cu²⁺ cations replacement, causes relevant modifications in the lattice parameter (c), crystallite size (D), dislocation density (δ), strain (ε_c) and stress (σ_c) of the hexagonal structure wurtzite from ZnO. The Co and Cu cations inclusion in the ZnO host lattice, alto caused a decrease in the optical band gap energy (3.37 for 3.16 eV), which is related to the charge transfer between the 4f level electrons and the conduction band or valence band of ZnO. Finally, for all films thin the linear and non-linear optical constants were computed and analyzed, showing variations that depend on the concentration of the dopant cations.

Keywords (Co–Cu) co-doped ZnO \cdot Thin films \cdot Sol–gel process \cdot Spin coating \cdot XRD patterns

1 Introduction

The importance of linear and non-linear optical semiconductors (NLOs) lies in the optical properties within which light is propagated. Therefore, they are used in various applications such as: optical waveguides, optoelectronic apparatuses, optical switching, image treatment, optical signal processing, optical enquiry stocking, optical locating, high-speed optical connections, and after time appliances in biological and medical sciences (Nagaraja et al. 2013).

Zinc oxide (ZnO) thin films are extensively studied because they have high photoelectric possessions, high electrochemical stability and energy gap ($E_g = 3.37 eV$) at

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room temperature (Yan et al. 2020). The ZnO doped and codoped with different cations is inspected as an excellent strategy for changes and improves various physical properties such as, crystalline quality, reducing crystal defects and modulating the energy gap (Kompa et al. 2023; Andriotis and Menon 2015; Chaitra et al. 2017; Mohammedi et al. 2022). The ZnO properties have been studied from the insertion of a simple cations: Fe(Hadimani et al. 2018), Mg(Mahroug et al. 2019), Ni (Oudjertli et al. 2022), Al (Islam et al. 2019), Cu (Mohammedi et al. 2021), Al, Cu, Co and In (Kim et al. 2015), and with two simultaneous cations such as: (Co–Al) and (Ni–Cu) (Swapna and Reddy 2018; Ali et al. 2018), (Y–Fe) (Peña-Garcia et al. 2020), (Ni–Sr) (Peña-Garcia et al. 2023) Also, Goktas et al. (2018) reported the structural, optical and magnetic properties Co–Cu doped ZnO thin films that was annealed in air and argon atmosphere. The NLOand ZnO thin films doped with Na (Deekshitha et al. 2019), Zr (Bahedi et al. 2009a), and Ce (Chen et al. 2020) have demonstrated optical improved properties (Peng et al. 2018).

Other simple oxides, such as CoO, have been studied by Z-Scan by various researchers (Chouhan et al. 2017). Also, the study of NLO properties of ZnO structures by Z-Scan has been madeby different authors (Mostafa et al. 2021). For example, Mustafa et al. examined the NLO properties of ZnO samples doped and co-doped with Zn and Ag prepared with PLD technique. They reported an enhancement in the NLO properties for the Ag/Zn/ZnO co-doped sample, which may be suitable for optical applications (Ali et al. 2018). Furthermore, non-linear optical response $\chi^{(3)} = 20.12 \times 10^{-12}$ on Zr- doped ZnO films utilizing the spray pyrolysis technique was reported (Bahedi et al. 2009b).

Based on this argument, in this work, Co-Cuco-doped ZnO thin films have been obtained on glass substrate, combining the sol–gel method and spin-coating technique. Specifically, films were obtained from the compound with general chemical formula: $Zn_{1-x-z}Co_xCu_zO$, [(x; z) = (0.00; 0.00), (0.02; 0.02), (0.04; 0.04) and (0.06; 0.06)]. We focused on the study of the simultaneous addition of Co and Cu cations on the morphological, structural, and optical linear and non-linear properties (second-degree refractive index and third-degree electrical susceptibility). Our study aims to amplify the optical applications of these films, specifically, in the transparent conductor screen.

2 Experimental method

2.1 Method of preparation

For synthesis, we used the general chemical formula: $Zn_{1-x-z}Co_xCu_zO$, [(x; z)=(0.00; 0.00), (0.02; 0.02), (0.04; 0.04) and (0.06; 0.06)].We prepared a solution of initial concentration ($C_T=0.5$ M) and initial volume ($V_T=10$ ml). The raw materials, Zinc acetate dehydrates [Zn (CH₃COO)₂2H₂O], Cobalt (II) chloride dihydrate (CoCl₂.H₂O), and Copper (II) chloride dihydrate (CuCl₂.H₂O) were dissolved in 2-propanol by constant agitation. The Monoethanolamine (MEA) was used as a stabilizer in the solution. The solution was mixer at 65°C for 2 h and then left for 24 h at room temperature. The glass substrates were cleaned with ethanol and acetone for 10 min and dried. The sol was transformed in crystalline films using the spin coating technique (3000 rpm), with a heat treatment at 250 °C for 4 min to steam the solvents and organic residuum and then, at 500 °C. All samples were prepared under the same conditions, respecting the mixing at the atomic level.

2.2 Characterization method

The morphologies of the films were studied from images obtained in a FEI quanta FEG 200 (FESEM) field-emitting scanning electron microscope (30 kV) and equipped with an energy-dispersion X-ray (EDAX). The XRD patterns were measurement using a Rigaku Ultima IV diffractometer in the Bragg–Brentano configuration utilizing CuK α radiation (λ =1.54060 Å). The optical properties were analyzed by measurement obtained in a UV–visible spectrophotometer, Lambda 35 model (range of 300–800 nm). The transmission (T) and absorption (A) ranges are steeped, while the reflectance (R) is calculated using the formula: R=1–(T+A). Finally, the film thickness is measured by using the Claw-Tencor Alpha-Step D-500 stylus profiler.

3 Results and discussion

3.1 Morphology and chemical analysis

The morphology of the Co/Cu co-doped films are shown in Fig. 1a–d. It is evident from the images that, the surface morphology of the ZnO films is significantly assumed by deposition method and annealing time. The obtained films are composed of small spherical grains

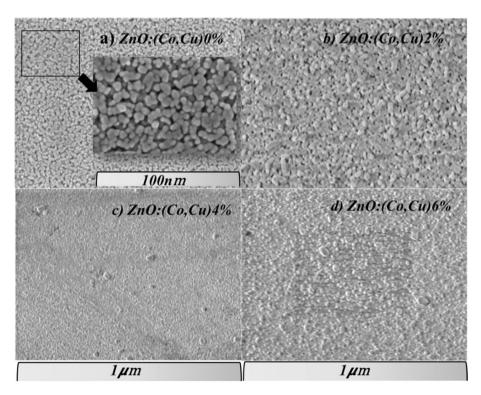


Fig.1 SEM images of (Co–Cu) co-doped ZnO thin films **a** x=0%, **b** x=2%, **c** x=4% and **d** x=6% as a function of (Co–Cu) contents

that present interstitial spaces; more apparent for the pure ZnO film. For co-doped films, it is notable that the interstitial spaces decrease, which may be an effect of the dopant cations that help to improve the films densification. On the other hand, the EDAX analysis was performed to determine the elements composition of the obtained films, (Fig. 2a–d). As observed, all films contain the Zn and O elements, while in the co-doped ZnO films, the cobalt (Co) and copper (Cu) elements are also observed (Figs. 2b–d), confirming its insertion in the ZnO crystal structure.

3.2 Structural characterization

Figure 3 displays the X-ray diffraction patterns of the prepared films. Note that, all films have a well crystalline wurtzite hexagonal structure, typical of zinc oxide; that has been confirmed by the crystallographic card (*JCPDS No. 36-1451*). In addition, no additional phase of: Co, Cu, CuO, Cu₂O, Co₂O₄ and Co₃O₄ was observed in the XRD spectra (Goktas

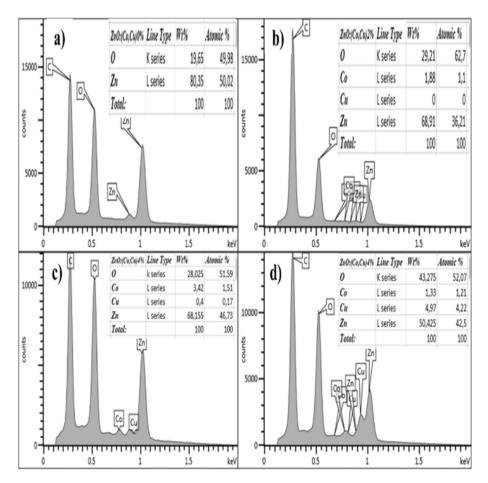
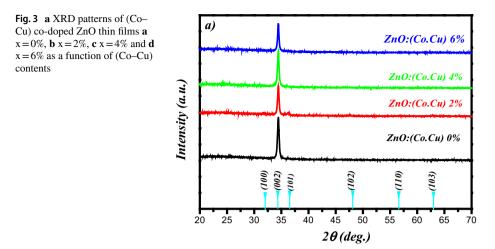


Fig. 2 EDAX spectra and table of concentration of (Co–Cu) co-doped ZnO thin films **a** x=0%, **b** x=2%, **c** x=4% and **d** x=6% as a function of (Co–Cu) contents



2018). It is important to emphasize that all films present a preferential orientation in the (002) direction. Many researchers believe that the more stable crystals level, as well as, the minimum free energy of surface, for ZnO films, is associated to the (002) plane (Mhamdi et al. 2013; Baghdad et al. 2017).

The crystal lattice parameter, (c) (Lupan et al. 2010), crystallite size (D) (Sengupta et al. 2013), dislocation density (δ) (Williamson and Smallman 1956), strain (ε_c) and stress (σ_c) (Mia et al. 2017; Muchuweni et al. 2017) were obtained using the subsequent formulas:

$$d_{hkl} = \frac{\lambda}{2\sin}, \frac{1}{d_{hkl}^2} = \frac{4}{3} \left(\frac{h^2 + hk + k^2}{a^2} \right) + \frac{l^2}{c^2}$$
(1)

$$u = \frac{a^2}{3c^2} + \frac{1}{4}, L = \sqrt{\left(\frac{a^2}{3} + \left(\frac{1}{2} - u\right)^2 c^2\right)}$$
(2)

$$D = \frac{0.9\lambda}{\left(\beta_{obs}^2 - \beta_{ins}^2\right)^{1/2} \cos\theta}, \delta = \frac{1}{D^2}$$
(3)

Here λ is the X-ray wavelength ($\lambda_{CuK_a} = 1.54060 \text{ Å}$), $\beta = (\beta_{obs}^2 - \beta_{ins}^2)^{1/2}$ is the full width of the peak at half maximum (*FWHM*) once corrected in radians and θ is the Bragg diffraction angle.

$$\varepsilon_c = \frac{Cfilm - Cbulk}{Cbulk} 100\%, \sigma_c = -2.33 \times 10^{11} \left(\frac{C_{film} - C_{bulk}}{C_{bulk}}\right) \tag{4}$$

where $c_{\rm film}$ and $c_{\rm bulk}$, are the lattice parameters of the prepared films and bulk ZnO, respectively.

As shown in Table 1, the lattice parameter (*c*) values for co-doped films are inferior to the obtained for pure ZnO films. The results were influenced by the difference between the ionic radius of copper ($r_{Cu+2}=0.72\text{ Å}$) and that of cobalt ($r_{Co+2}=0.65\text{ Å}$), compared to the zinc ($r_{Zn+2}=0.74\text{ Å}$) (Sreedhar et al. 2016; Benzitouni et al. 2017). In addition, we note that the Co and Cu inclusion in the ZnO structure increased the

Samples	2θ(deg.)	FWHM	c(Å)	D(nm)	$\delta(10^{-3}/nm^2)$	$\varepsilon_{\rm c} (10^{-3})$	$\sigma_{c}(\text{GPa})$
Un-doped ZnO	34.414	0.330	5.205	25.140	1.582	0.1096	-0.2554
ZnO:Co 2%:Cu 2%	34.431	0.302	5.203	28.701	1.213	1.258	-0.147
ZnO:Co 4%:Cu 4%	34.436	0.301	5.202	28.131	1.263	1.254	-0.114
ZnO:Co 6%:Cu 6%	34.425	0.252	5.204	34.472	0.841	1.050	-0.186

Table 1 The peak position 2θ , FWHM, lattice parameter (a and c), grain size (D), dislocation density (δ), strain (ε_c) and stress (σ_c) of the (Co–Cu) co-doped ZnO thin films

crystalline size, ranging from 26.276 nm for the pure ZnO film to 34.472 nm for the 6% Co–Cu co-doped ZnO film. This result could be attributed to the fact that, the co-doping may have ameliorated the crystal goodness, favoring the growth and nucleation mechanisms (Narayanan and Deepak 2018; Kaphle and Hari 2018). In addition, the crystal-lite size increase may be related to the fact that the films have preferential orientation in the c-axis. On the other hand, we note variations in the strain values, increasing the Co–Cu dopants concentration ratios. Finally, negative stress values point that the crystal structure is in a stress state due to the dopant atoms influence, obtaining method and temperature, as well as the variance in thermal coefficient factor between the film and substrate (Joshi et al. 2016).

3.3 Optical characterization

Figure 4 exhibits the optical transmittance and reflectance spectra of the pure and codoped ZnO films. In the visible spectrum, the optical transmittance of co-doped films is relatively low, compared to the pure ZnO film; around of 42% for the film co-doped at 2% and 85% for pure ZnO film. For wavelengths less than of 400 nm, the transmittance decreases rapidly, which confirms that films have shift absorption. The optical absorption coefficient $\alpha(\lambda)$ was determined for various photon energies using the transmission spectra and the equation (Gumus et al. 2006):

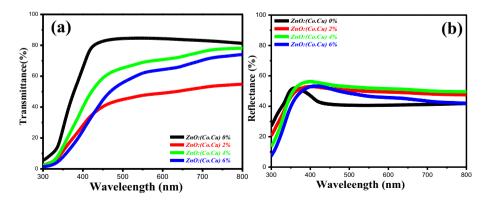


Fig. 4 a Optical transmittance and b reflectance of (Co–Cu) co-doped ZnO thin films as a function of wavelength

$$\alpha = \frac{\mathrm{Ln}(\frac{1}{\mathrm{T}})}{\mathrm{t}}$$
(5)

Here T is the transmittance and t, is the thickness of the films, that is equal to 150 nm in our case. The ZnO is a direct gap semiconductor. Thus, its energy-gap (E_g) could be deduced from the x interception of the linear extrapolation of the curve $(ahv)^2$ as a function of photon energy radiation (hv) (inset of Fig. 5) by the Tauc's relationship (Kaphle and Hari 2018):

$$(\alpha h v)^{n} = B(h v - Eg)$$
(6)

where B is a constant and n=2, is used for the direct-gap energy.

In Fig. 5, the energy band-gap values (E_g) are presented as a function of Co–Cu dopants concentration. We can observe that the energy band gap decreases linearly increasing the Co–Cu concentration (3.37–3.16 eV for Co–Cu concentration ranging from 0.00 to 0.06). The energy-gap decrease can be explained by the atomic disorder (oxygen vacancy and zinc interstitial defects) generated in the ZnO structure due to the dopant cations inclusion. The defects provoke free electrons, with minor energy than the ZnO in the valence band, generating others electronic levels in the ZnO band gap, which will contribute to the energy band gap band reduction. In addition, some authors, attribute the variation in the energy gap to the charge transfer between the 4f level electrons and the conduction band or valence band of ZnO (Diouri et al. 1985; Elilarassi and Chandrasekaran 2010; Li et al. 2011). On the other hand, the small variance in the electronegativity between Cu (1.9), Co (1.88) and Zn (1.65) cations can also lead to a narrowing of the energy band gap (Ferhat et al. 2009).

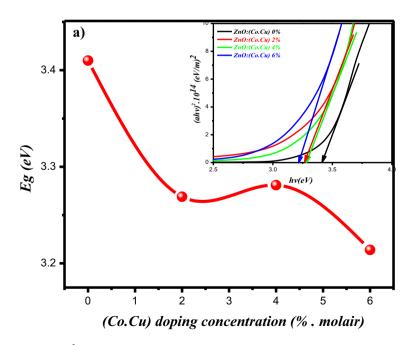


Fig. 5 a: Plot of $(\alpha h \upsilon)^2$ versus $(h \upsilon)$ b: band-gap energy versus (Co–Cu) concentration

3.3.1 Linear optical parameters

The extinction coefficient (*k*), refractive index (*n*), real and imaginary parts (ε_r and ε_i) of the dielectric constant and optical conductivity (σ_{opt}) (Islma and Podder 2009; Caglar et al. 2007, 2008) have been calculated as follows:

$$k = \frac{\alpha \lambda}{4\pi} \tag{7}$$

$$n = \left(\frac{1+R}{1-R}\right) + \sqrt{\frac{4R}{(1-R)^2} - k^2}$$
(8)

$$\varepsilon_{\rm r} = {\rm n}^2 - {\rm k}^2 \varepsilon_{\rm i} = 2 {\rm n} {\rm k} \tag{9}$$

$$\sigma_{\rm opt} = \frac{\omega}{4\pi} \sqrt{\varepsilon_{\rm i}^2 + (1 - \varepsilon_{\rm r})^2} \tag{10}$$

where $\omega = hv/\hbar\lambda$, α is the absorption coefficient and R represents the optical reflectance. The optical constants versus the wavelength are shown in Fig. 6. It is to be noted that in the visible field n is 1.75 for ZnO. This value increases for co-doped samples until it reaches about 2.5. Similar results have been reported in the literature by other authors (Hamidi et al. 2018; Istrate et al. 2019). Because of weak absorption, K is almost non-existent. The values of ε_r vary between 3 and 6 and the values of ε_i are almost zero. It can be said that the electric charge polarization varies with the electric range variation of incident wave. We also note an enhancement in the refractive index, damping factor, and the imaginary part appearance. This is owing to the attendance of great absorption and electron transfer in ultraviolet fields (Mahdhi et al. 2018).

On the other hand, the Fig. 7a displays the change of optical conductivity for the Co–Cu co-doped ZnO films in terms of the wavelength. As observed, the conductivity changes are like those of the absorption and the imaginary part of the dielectric constant. In addition, the optical conductivity was deduced in terms of the Co–Cu dopant percentages and are shown in Fig. 7b. Note that the optical conductivity values vary between 1.68×10^{16} and 1.30×10^{16} (1/s). Compared to the previous report, for Cu-doped ZnO thin films, there was an improvement due to the simultaneous Co and Cu dopant cations insertion in the ZnO crystal structure (Mohammedi et al. 2021).

The refractive index at elevated frequencies (n_{∞}^2) (Walton and Moss 1963), the individual oscillator energy of electronic transitions (E₀) and the dispersal energy (E_d) (Caglar et al. 2007) were calculated using the following equations:

$$\frac{n_{\infty}^2 - 1}{n^2 - 1} = 1 - \left(\frac{\lambda_0}{\lambda}\right)^2 \tag{11}$$

$$n^{2} = 1 + \frac{E_{d}E_{0}}{E_{0}^{2} + (hv)^{2}}$$
(12)

Plotting $(n_{\infty}^2 - 1)^{-1}$ in terms of λ^{-2} , the value of the n_{∞}^2 may be deduced from the intersection with the ordinal axis of Fig. 8a. Plotting $(n^2 - 1)^{-1}$ in terms of $(hv)^2$, the values of

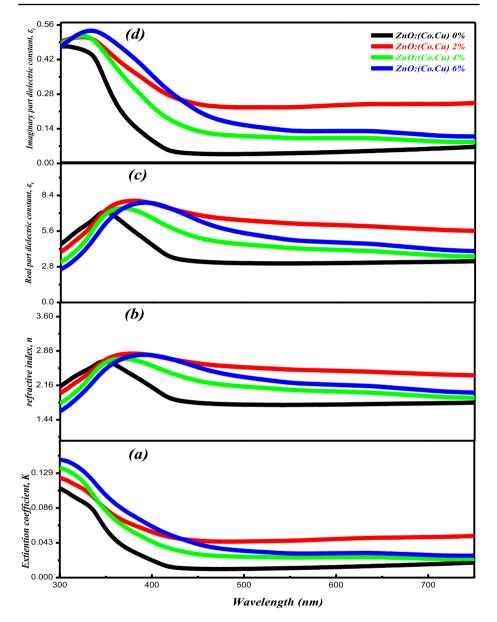


Fig. 6 a: Refractive index n, b: extinction coefficient k, c: real part of dielectric constant ε_r and d: imaginary part of dielectric constant ε_r of the (Co–Cu) co-doped ZnO thin films with various wavelengths

 E_0 and E_d can be calculated by intersecting the order axis and the slope as shown in Fig. 8. The E_0 , E_d and n_∞ values for the Co–Cu co-doped ZnO thin films are illustrated in the Table 2. Note that the values of E_d and n_∞ are improved increasing the Co–Cu concentration and these results are almost consistent for reported by Gao Xiao-Yong et al. (Gao et al. 2010). All the values of E_0 of the doped films are higher than that of the undoped film; on the other hand, E_0 decreases with the increase of the doping concentration.

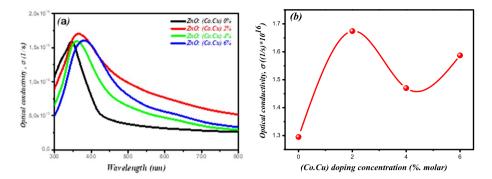


Fig. 7 Optical conductivity of (Co-Cu)co-doped ZnO, a: versus wavelength and b: versus Co-Cu concentration

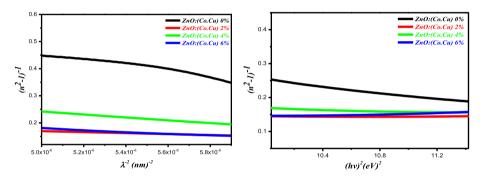


Fig.8 a: The plot of $(n^2-1)^{-1}$ various $(\lambda)^{-2}$ and b: the plot of $(n^2-1)^{-1}$ various $(hv)^2$ of the (Co–Cu) co-doped ZnO thin films

Table 2Optical dispersionparameters of (Co–Cu) co-dopedZnO thin films	Samples	$E_0 (eV)$	$E_{d}\left(eV ight)$	$\varepsilon i = n_{\infty}^2$
	Un-doped ZnO	4.216	5.929	3.227
	ZnO:Co 2%:Cu 2%	6.899	14.494	6.882
	ZnO:Co 4%:Cu 4%	5.513	18.136	5.132
	ZnO:Co 6%:Cu 6%	4.949	20.203	6.524

3.3.2 Nonlinear optical parameters

The investigation of the interaction of the electromagnetic field with the physical medium, where the interaction of the electric field with the incidental wave is of non-linear polarization is shown by the subsequent formula (Frumar et al. 2003)

$$P_{NL} = \chi^{(1)}E + \chi^{(2)}E2 + \dots \chi^{(n)}E^n$$
(13)

Here, $\chi^{(1)}$, $\chi^{(2)} E^2$ and $\chi^{(3)} E^3$ are the polarizabilities, $\chi^{(1)}$ is the linear optical susceptibility, and $\chi^{(2)}$ and $\chi^{(3)}$ are the second- and third-order nonlinear optical susceptibility, respectively.

The n becomes non-linear according to the following equation,

$$n(\lambda) = n_0(\lambda) + n^{(2)}(E^2)$$
(14)

Here , $n^{(0)}$ is linear, n and $n^{(2)}$ is nonlinear. The n is allied to the electric field power. Various quasi-empirical equations are nominated to calculate the third-order non-linear optical susceptibility $\chi^{(3)}$ and the non-linearn⁽²⁾. Amongst these relations, one may obtain the Miller formula generalized in the subsequent relation (Ticha and Tichy 2002),

$$\chi^{(3)} = A(\chi^{(1)}) \tag{15}$$

According to Adair et al. (Ferhat et al. 2009), the value of the constant (A) is equal to 1.79×10^{-10} (for $\chi^{(1)}$ in esu). For a different type of materials,

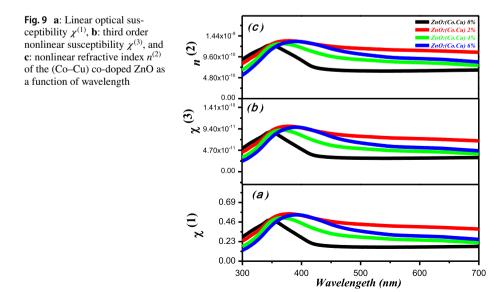
$$\chi^{(1)} = \frac{(n^2 - 1)}{4\pi} \tag{16}$$

Considering the Eq. (13), at small frequencies $hv \rightarrow 0$ and $n = n_0$, $(\chi^{(1)})$ is explained by:

$$\chi^{(1)} = \frac{E_d}{E_0 4\pi}$$
(17)

$$n^{(2)} = \frac{12\pi\chi^{(3)}}{n_0} \tag{18}$$

We have calculated the quantities of $\chi^{(1)}$, $\chi^{(3)}$ and $n^{(2)}$ in terms of the wavelength (Fig. 9a–c). We notice that the values of these parameters increase in the ultraviolet field, but they are almost constant in the visible field. The NLO constants values increase with the Co–Cu co-dopant cations insertion (Table 3). This phenomenon is related to a crystallization improved of the samples (Table 1). Everything indicates that our ZnO thin films co-doped with Co and Cu are candidate for NLO applications.



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Samples	n_0	$\chi^{(1)}$	$\chi^{(3)}$, esu	<i>n</i> ⁽²⁾ , esu
Un-doped ZnO (present work)	1.815	0.111	2.004×10^{-11}	4.161×10^{-10}
ZnO:Co 2%:Cu 2%(present work)	2.346	0.167	2.994×10^{-11}	4.808×10^{-10}
ZnO:Co 4%:Cu 4% (present work)	1.894	0.261	4.688×10^{-11}	9.326×10^{-10}
ZnO:Co 6%:Cu 6% (present work)	1.976	0.324	5.816×10^{-11}	1.109×10^{-9}
Co-doped ZnO Shaaban et al. (2016)	_	0.13-0.20	$0.48 - 2.72 \times 0^{-13}$	1.89–9.11 9×10 ⁻¹⁰
Sn-doped ZnO Ganesh et al. (2017)	-	0.1-0.91	$0.51 - 9.09 \times 10^{-11}$	$0.5 \times 10^{-10} - 1 \times 10^{-9}$
Cu-doped ZnO Ganesh et al. (2018)	-	0.09-0.19	$0.25 - 2.25 \times 10^{-13}$	$0.25 - 4.59 \times 10^{-12}$

Table 3 Nonlinear optical parameters of reported and present work on ZnO thin films

4 Conclusions

In the present study, thin films of ZnO co-doped with cations of Co^{2+} and Cu^{2+} were obtained utilizing the sol–gel method and spin coating technique. The morphological, structural, and optical linear and nonlinear properties are analyzed in detail. The SEM images revealed that the pure ZnO film is composed by small spherical grains that present interstitial spaces, while the films obtained from the simultaneous Co and Cu insertion in the ZnO structure are more dense and interstitial spaces disappear. The EDAX data confirm the attendance of Co, Cu, Zn and O elements in the ZnO thin films. The X-ray diffraction patterns confirmed the single-phase formation of ZnO and preferential orientation in the (002) direction. In addition, the Zn²⁺ cations by Co²⁺ and Cu²⁺ cations replacement, provokes significant variations in the lattice parameter (c), crystallite size (D), dislocation density (δ), strain (ε_c) and stress (σ_c) of the hexagonal structure wurtzite from ZnO. In general, the results obtained in this work provide new alternatives for designing thin films with optoelectronics applications. This is because the layers have the desired nonlinear optical properties to effectively transparent conductive screens.

Author contributions AM: Performed the experiences of this work. OM: Performed the experiences of this work. MI: Supervised and developed the experience. BM and RP-G: Verified the development of experiences. NB: Supervised the findings of this work. All authors discussed the results and contributed to the final manuscript.

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Declarations

Conflict of interest The authors declare that they have no conflicts of interest.

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